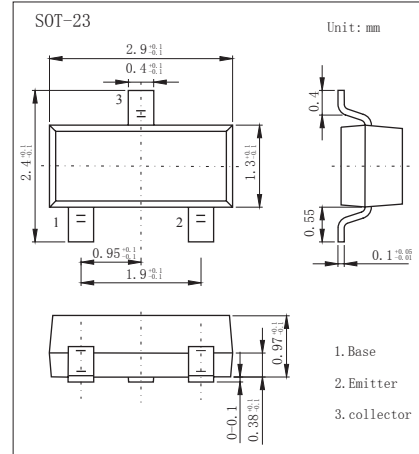


**PNP Transistors**

**KTA1504**

■ Features

- Excellent hFE Linearity
- Low Noise
- Complementary to KTC3875



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V <sub>CBO</sub>	-50	V
Collector - Emitter Voltage	V <sub>CEO</sub>	-50	
Emitter - Base Voltage	V <sub>EBO</sub>	-5	
Collector Current - Continuous	I <sub>C</sub>	-150	mA
Base Current	I <sub>B</sub>	-30	
Collector Power Dissipation	P <sub>C</sub>	150	mW
Thermal Resistance From Junction To Ambient	R <sub>θJA</sub>	833	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature range	T <sub>stg</sub>	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V <sub>CBO</sub>	I <sub>C</sub> = -100 μA, I <sub>E</sub> =0	-50			V
Collector- emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = -1 mA, I <sub>B</sub> =0	-50			
Emitter - base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = -100 μA, I <sub>C</sub> =0	-5			
Collector-base cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -50 V, I <sub>E</sub> =0			-100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> =0			-100	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-100 mA, I <sub>B</sub> =-10mA			-0.3	V
Base - emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-100 mA, I <sub>B</sub> =-10mA			-1.2	
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = -6V, I <sub>C</sub> = -2mA	70		400	
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0, f=1MHz			7	pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -10V, I <sub>C</sub> = -1mA	80			MHz

■ Classification of h<sub>FE</sub>

Type	KTA1504-O	KTA1504-Y	KTA1504-G
Range	70-140	120-240	200-400
Marking	ASO	ASY	ASG